

NPN 100mA 50V Digital Transistors (Bias Resistor Built-in Transistors)

Parameter	Value
V _{CEO}	50V
I _C	100mA
R ₁	4.7kΩ

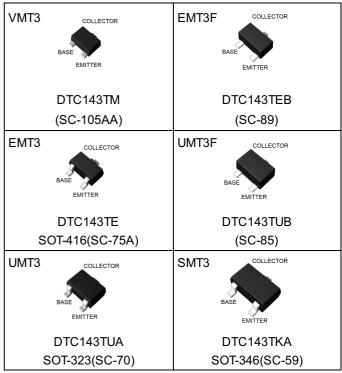
Features

- 1) Built-In Biasing Resistor
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 4) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 5) Complementary PNP Types: DTA143T series
- 6) Complex transistors: EMH3/ UMH3N/ IMH3A/ EMG3/ UMG3N/ FMG3A (PNP type)
- 7) Lead Free/RoHS Compliant.

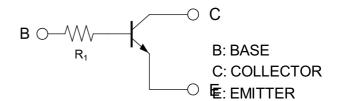
Application

Switching circuit, Inverter circuit, Interface circuit, Driver circuit

Outline



•Inner circuit



Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
DTC143TM	VMT3	1212	T2L	180	8	8000	03
DTC143TEB	EMT3F	1616	TL	180	8	3000	03
DTC143TE	EMT3	1616	TL	180	8	3000	03
DTC143TUB	UMT3F	2021	TL	180	8	3000	03
DTC143TUA	UMT3	2021	T106	180	8	3000	03
DTC143TKA	SMT3	2928	T146	180	8	3000	03

● Absolute maximum ratings (T_a = 25°C)

Pa	arameter	Symbol	Values	Unit
Collector-base voltage		V_{CBO}	50	V
Collector-emitter voltage			50	V
Emitter-base voltage			5	V
Collector current		I _C	100	mA
	DTC143TM		150	
	DTC143TEB		150	\A/
Davie a discipation	DTC143TE	P _D *1	150	
Power dissipation	DTC143TUB	P _D .	200	mW
	DTC143TUA		200	
	DTC143TKA		200	
Junction temperature		T _j	150	°C
Range of storage temperate	ture	T _{stg}	-55 to +150	°C

● Electrical characteristics (T_a = 25°C)

Davanatas	Symbol Conditions		Values			1.1
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 50μA	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	-	-	0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	0.5	μA
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{C} / I_{B} = 5 \text{mA} / 0.25 \text{mA}$	-	-	0.15	V
DC current gain	h _{FE}	V _{CE} = 5V, I _C = 1mA	100	250	600	-
Input resistance	R ₁	-	3.5	4.7	5.9	kΩ
Transition frequency	f _T *2	V _{CE} = 10V, I _E = -5mA, f = 100MHz	-	250	-	MHz

^{*1} Each terminal mounted on a reference footprint

^{*2} Characteristics of built-in transistor

● Electrical characteristic curves(Ta=25°C)

Fig.1 Grounded emitter propagation characteristics

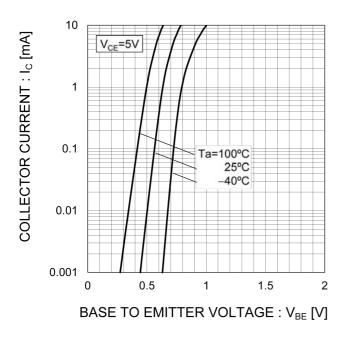


Fig.2 Grounded emitter output characteristics

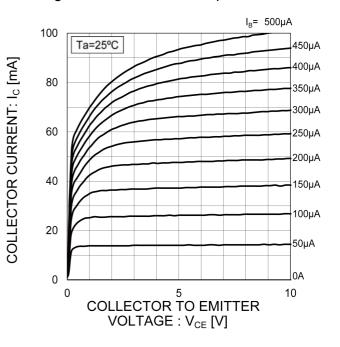


Fig.3 DC Current gain vs. Collector Current

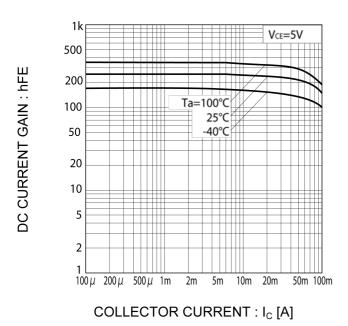
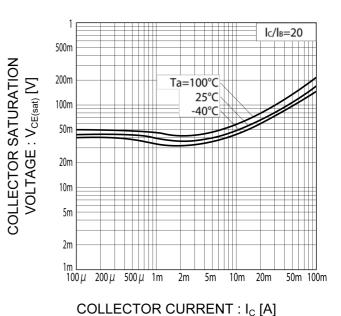
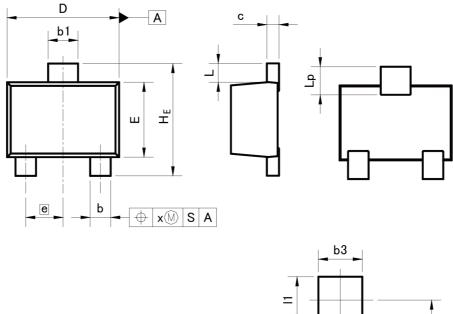


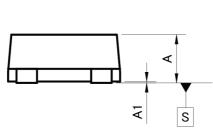
Fig.4 Collector-emitter saturation voltage vs.

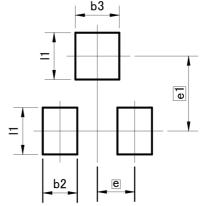
Collector Current











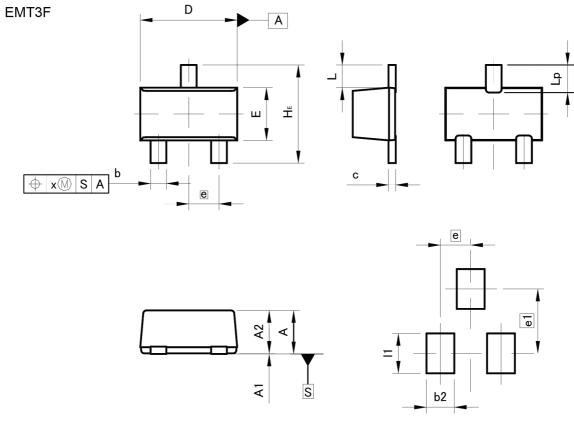
Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM -	MILIM	ETERS	INC	HES
DIM [MIN	MAX	MIN	MAX
Α	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
С	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
е	0.4	40	0.02	
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	0.012
Lp	0.20	0.40	0.008	0.016
x	=	0.10	=	0.004

DIM	MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
b2	-	0.37		0.015
b3		0.47		0.019
e1	0.	0.80		031
11	-	0.50	-	0.020

Dimension in mm/inches





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

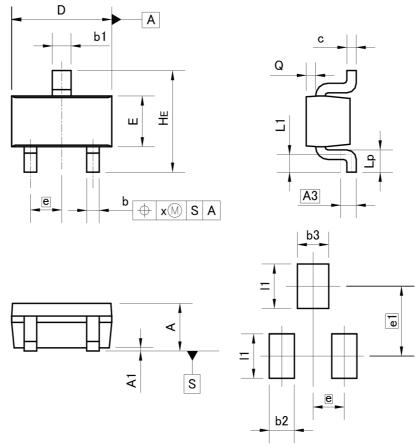
DIM	MILIM	ETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	0.65	0.85	0.026	0.033
A1	0.00	0.10	0.000	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
С	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	0.76	0.96	0.030	0.038
е	0.9	50	0.0	20
HE	1.50	1.70	0.059	0.067
L	0.3	37	0.0	15
Lp	0.35	0.55	0.014	0.022
х	=	0.10	=	0.004

DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
b2	_	0.46	<u>—</u>	0.018
e1	≂	1.05	<i>π</i> .	0.041
11	-	0.65	 :	0.026

Dimension in mm/inches



EMT3



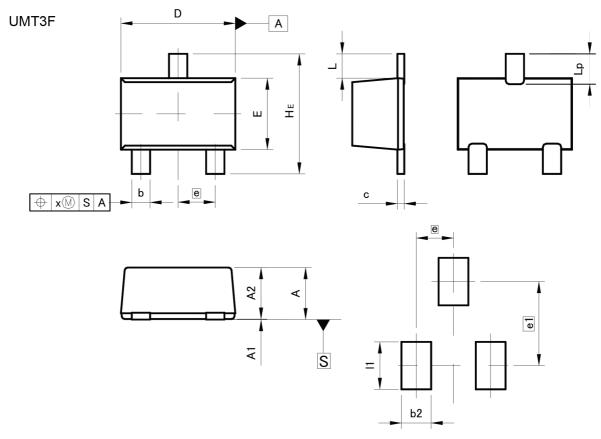
Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	0.60	0.80	0.024	0.031
A1	0.00	0.10	0.000	0.004
A3	0.	25	0.0	10
b	0.15	0.30	0.006	0.012
b1	0.25	0.40	0.010	0.016
С	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
е	0.	50	0.0	20
HE	1.40	1.80	0.055	0.071
L1	0.10	 :	0.004	
Lp	0.15	55 3:	0.006	TT.
Q	0.05	0.25	0.002	0.010
x	— 1	0.10	_	0.004

DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
b2	77.L	0.40	-53	0.016
b3		0.50	-	0.020
e1	1.	10	0.0	043
11	12 5	0.70	-	0.028

Dimension in mm/inches





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

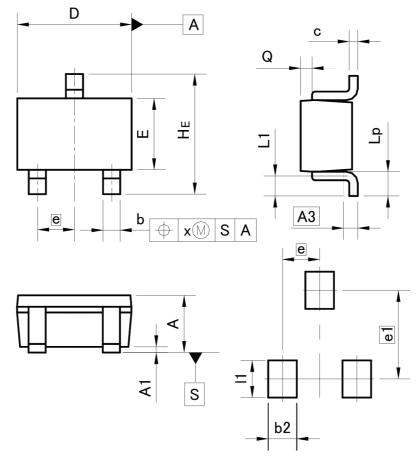
DIM -	MILIM	ETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	0.85	1.05	0.033	0.041
A1	0.00	0.10	0.000	0.004
A2	0.80	1.00	0.031	0.039
b	0.27	0.42	0.011	0.017
С	0.08	0.18	0.003	0.007
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.0	65	0.0	26
HE	2.00	2.20	0.079	0.087
L	0.4	43	0.0	17
Lp	0.43	0.63	0.017	0.025
х	=	0.10	<u> </u>	0.004

DIM -	MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
b2	_	0.52	<u>—</u>	0.020
e1	1.	1.47		058
11	-	0.83		0.033

Dimension in mm/inches



UMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

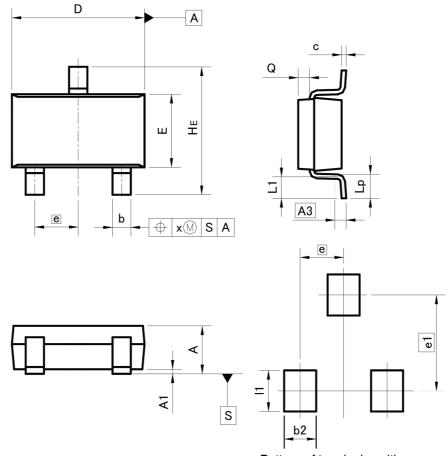
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
Α	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
х	=	0.10	=	0.004

DIM	MILIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
b2		0.50	_	0.020
e1	1.55		0.061	
11	_	0.65	_	0.026

Dimension in mm/inches



SMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
Α	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
С	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
е	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
x	20	0.10	722	0.004
у	<u> </u>	0.10	_	0.004
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	=	0.60	_	0.024

Dimension in mm/inches

e1



0.035

0.083

0.90

2.10

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